L Number	Hits		DB	Time stamp
_	887626	gate	USPAT;	2004/09/24 14:2:
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	639571	mos\$1fet or mis\$1fet or fet or mos or pmos	USPAT;	2004/09/24 14:3
		or nmos or field adj4 (transistor or	US-PGPUB;	
		device)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	83577	· · · • · · · · · · · · · · · · · ·	USPĀT;	2004/09/24 14:32
		thickness	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	2741827	insulat\$4 or di\$1electric or oxide or	IBM_TDB	2004/09/24 14:43
_	2/4102/	"sio.sub."\$1	USPAT; US-PGPUB;	2004/03/24 14:4\
		510.3ub. 91	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	133420	gate adj5 (insulat\$4 or di\$1electric or	USPAT;	2004/09/25 14:10
		oxide or "sio.sub."\$1)	US-PGPUB;	
		· ·	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	484543	high adj3 (voltage or power)	USPAT;	2004/09/24 14:45
			US-PGPUB;	
		·	EPO; JPO;	
	ĺ		DERWENT;	
_	328173	low adj3 (voltage or power)	IBM_TDB USPAT;	2004/09/24 14:40
	3201/3	row adjo (vortage of power)	US-PGPUB;	2007/03/24 14:41
			EPO; JPO;	
		•	DERWENT;	
			IBM TDB	
-	978	gate with thick with (high adj3 (voltage	USPAT;	2004/09/24 14:40
7		or power))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	635		IBM_TDB	2004/00/04 14 17
-	877	9	USPAT;	2004/09/24 14:4
		power))	US-PGPUB; EPO; JPO;	
			DERWENT;	
		٦	IBM TDB	
_	301	(gate with thick with (high adj3 (voltage	USPAT;	2004/09/24 14:49
		or power))) and (gate with thin with (low	US-PGPUB;	
		adj3 (voltage or power)))	EPO; JPO;	
		· · · · · · · · · · · · · · · · · · ·	DERWENT;	
			IBM_TDB	
-	300	((gate with thick with (high adj3 (voltage	USPĀT;	2004/09/24 16:16
		or power))) and (gate with thin with (low	US-PGPUB;	
		adj3 (voltage or power)))) and ((insulat\$4	EPO; JPO;	
		or di\$lelectric or oxide or "sio.sub."\$1)	DERWENT;	
		or ((multiple or differen\$2 or various) adj4 thickness))	IBM_TDB	
_	1461	438/591.ccls. or 438/585.ccls.	USPAT;	2004/09/24 16:04
	1401	450/071.0013. OI 430/003.0018.	US-PGPUB;	2003/03/24 10:04
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
- !	1202	(438/591.ccls. or 438/585.ccls.) and (gate	USPĀT;	2004/09/24 16:04
		adj5 (insulat\$4 or di\$1electric or oxide	US-PGPUB;	
		or "sio.sub."\$1))	EPO; JPO;	
	h [] [DERWENT;	
	400	///20/501 3 420/505 3 3 3	IBM_TDB	0004/00/01 == ==
	490	((438/591.ccls. or 438/585.ccls.) and	USPAT;	2004/09/24 16:05
-			tto popus	
-		(gate adj5 (insulat\$4 or di\$1electric or	US-PGPUB;	
_		(gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1))) and thick and thin	US-PGPUB; EPO; JPO; DERWENT;	

156505 Rf or hydrofluoric					
- 4732 hto or high adj2 temperature adj2 oxide - 503341 etch\$3 - 2493898 resistance or resistant - 2493898 resistance or resistant - 4 (hf or hydrofluoric) same (hto or high adj2 temperature adj2 oxide) - 2524462 etch\$3 or removed - 2524462 etch\$3 or removed - 182885 bhf or boe or (hf or hydrofluoric) - 101 (bhf or boe or (hf or hydrofluoric)) same (hto or high adj2 temperature adj2 oxide) - 38286 same (etch\$3 or removed) - 101 (bhf or boe or (hf or hydrofluoric)) same (hto or high adj2 temperature adj2 oxide) - 272462 etch\$3 or removed - 101 (bhf or boe or (hf or hydrofluoric)) same (hto or high adj2 temperature adj2 oxide) - 102 (bhf or boe or (hf or hydrofluoric)) same (hto or high adj2 temperature adj2 oxide) - 272462 same (etch\$3 or removed) - 103 (bhf or boe or (hf or hydrofluoric)) same (hto or high adj2 temperature adj2 oxide) - 10404321 benefit or advantag\$5 - 10404321 benefit or advantag\$5 - 10404321 benefit or advantag\$5 - 104064321 benefit or advantag\$5 - 105066666666666666666666666666666666666	-	156505	hf or hydrofluoric		2004/09/24 16:17
A					
IBM TOB					
101					
US-PGPUB; EPO, JPC; DERMENT; IBM TDB USFAT; USFAT; USFAT; USFAT;			l		
- 503341 etch33 etch33 EPO, JPO, DERMERT; ISM TOB USPAT; US-POURS, PEO, JPO, DERMERT; PEO, JPO, DE	-	4732	hto or high adj2 temperature adj2 oxide		2004/09/25 14:07
- 503341 etch\$3					
Sold etch\$3 etch\$3 Sech\$3 Sech\$7 US-FCPUB; EPO, JPO; DERMENT; IND TOB USPAT; US-FCPUB; EPO, JPO; J				· ·	
- 2493898 resistance or resistant					
- 2493898 resistance or resistant		502241		_	0004/00/04 16 10
- 2493898 resistance or resistant	_	503341	etcn\$3		2004/09/24 16:18
- 2493898 resistance or resistant					
TEM TDB USPAT: US-PGPUB; EPO; JPO; DERMENT; EM TDB USPAT: US-PGPUB; EPO; J					
- 2493898 resistance or resistant					
- 4 (hf or hydrofluoric) same (hto or high adj2 temperature adj2 oxide) same etch33 same (resistance or resistant) - 2524462 etch33 or removed - 182885 bhf or boe or (hf or hydrofluoric) - 101 (bhf or boe or (hf or hydrofluoric)) USPAT; US-PGPUB; EFO, JPO; DERMENT; IEM TDB USPAT; US-PGPUB; USPAT; US-	l _	2493898	resistance or resistant		2004/09/24 16:19
PEO, JPG, DERMENT; IBM TDB USPAT; US-PGEUB; EPO, JPG, DERMENT; IBM TDB USPAT;		2475070	lesistance of lesistant		2004/03/24 10:13
- 4 (hf or hydrofluoric) same (hto or high adj2 temperature adj2 oxide) same etch\$3					
A					
- 4 (hf or hydrofluoric) same (hto or high adj2 temperature adj2 oxide) same etch\$3 same (resistance or resistant) - 2524462 etch\$3 or removed - 182885 bhf or boe or (hf or hydrofluoric) - 101 (bhf or boe or (hf or hydrofluoric)) same (hto or high adj2 temperature adj2 oxide) - 4732 hto or high adj2 temperature adj2 oxide - 10404321 benefit or advantag\$5 - 140 (hto or high adj2 temperature adj2 oxide) - 133420 gate adj5 (insulat\$4 or di\$lelectric or oxide or "sio.sub."\$1) - 228 (hto or high adj2 temperature adj2 oxide) - 229 (hto or high adj2 temperature adj2 oxide) - 22004/09/25 14:19 - 22004/09/25 14:20 - 22004/09/25 14:20 - 22004/09/25 14:20					į
adj2 temperature adj2 oxide) same etch\$3 SP, JPO; DERMENT; Same (resistance or resistant) SP, JPO; DERMENT; SAME (resistance or resistant) SP, JPO; DERMENT; SAME (resistance or resistant) SP, JPO; DERMENT; SP, JPO; DERMENT; SP, JPO; DERMENT; SP, JPO; DERMENT; SEPO; JPO; DERMENT; SAME (hto or high adj2 temperature adj2 oxide) SPAT; US-PGPUB; SAME (etch\$3 or removed) SPAT; US-PGPUB; SAME (etch\$3 or removed) SPAT; US-PGPUB; SPO; JPO; DERMENT; SAME (etch\$3 or removed) SPAT; US-PGPUB; SPO; JPO; DERMENT; SAME (etch\$3 or removed) SPAT; US-PGPUB; SPO; JPO; DERMENT; SAME (etch\$3 or removed) SPAT; US-PGPUB; SPO; JPO; DERMENT; SAME (etch\$3 or removed) SPAT; US-PGPUB; SPO; JPO; DERMENT; SAME (etch\$3 or removed) SPAT; US-PGPUB; SPO; JPO; DERMENT; SAME (etch\$3 or removed) SPAT; US-PGPUB; SPO; JPO; DERMENT; SAME (etch\$3 or removed) SPAT; US-PGPUB; SPO; JPO; DERMENT; SAME (etch\$3 or removed) SPAT; US-PGPUB; SPO; JPO; DERMENT; SAME (etch\$4 or dislelectric or oxide or "sio.sub."\$1) SPAT; US-PGPUB; SPO; JPO; DERMENT; SAME (etch\$4 or dislelectric or oxide or "sio.sub."\$1) SPAT; US-PGPUB; SPO; JPO; DERMENT; SAME (etch\$4 or dislelectric or oxide or "sio.sub."\$1) SPAT; US-PGPUB; SPO; JPO; DERMENT; SPO; JPO; DER	l _	4	(hf or hydrofluoric) same (hto or high		2004/09/24 16:22
Same (resistance or resistant)		1			
- 2524462 etch\$3 or removed USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EP					
- 2524462 etch\$3 or removed	İ		,	l .	
- 2524462 etch\$3 or removed					
- 182885 bhf or boe or (hf or hydrofluoric) - 101 (bhf or boe or (hf or hydrofluoric)) same (hto or high adj2 temperature adj2 oxide) same (etch\$3 or removed) - 4732 hto or high adj2 temperature adj2 oxide) - 10404321 benefit or advantag\$5 - 10404321 benefit or advantag\$5 - 1040 (hto or high adj2 temperature adj2 oxide) with (benefit or advantag\$5) - 133420 gate adj5 (insulat\$4 or di\$lelectric or oxide or "sio.sub."\$1) - 133420 (hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$lelectric or oxide or "sio.sub."\$1) - 228 (hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$lelectric or oxide or "sio.sub."\$1) - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos	_	2524462	etch\$3 or removed		2004/09/24 16:23
- 182885 bhf or boe or (hf or hydrofluoric) - 101 (bhf or boe or (hf or hydrofluoric)) same (hto or high adj2 temperature adj2 oxide) same (etch\$3 or removed) - 4732 hto or high adj2 temperature adj2 oxide) - 10404321 benefit or advantag\$5 - 10404321 benefit or advantag\$5 - 1040 (hto or high adj2 temperature adj2 oxide) with (benefit or advantag\$5) - 133420 gate adj5 (insulat\$4 or di\$lelectric or oxide or "sio.sub."\$1) - 133420 (hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$lelectric or oxide or "sio.sub."\$1) - 228 (hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$lelectric or oxide or "sio.sub."\$1) - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos		1		US-PGPUB;	
TIME TOB		-			
- 182885 bhf or boe or (hf or hydrofluoric) USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; USPĀT USPĀT; USPĀT				DERWENT;	İ
- 101 (bhf or boe or (hf or hydrofluoric)) same (hto or high adj2 temperature adj2 oxide) same (etch\$3 or removed) - 4732 hto or high adj2 temperature adj2 oxide - 4732 benefit or advantag\$5 - 10404321 benefit or advantag\$5 - 140 (hto or high adj2 temperature adj2 oxide) - 140 (hto or high adj2 temperature adj2 oxide) with (benefit or advantag\$5) - 133420 gate adj5 (insulat\$4 or di\$lelectric or oxide or "sio.sub."\$1) - 133420 (hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$lelectric or oxide or "sio.sub."\$1) - 228 (hto or high adj2 temperature adj2 oxide) with teos (hto or high adj2 temperature adj2 oxide) with teos (hto or high adj2 temperature adj2 oxide) with teos (hto or high adj2 temperature adj2 oxide) with teos (hto or high adj2 temperature adj2 oxide) with teos (hto or high adj2 temperature adj2 oxide) DERWENT;				IBM TDB	
- 101 (bhf or boe or (hf or hydrofluoric)) same (hto or high adj2 temperature adj2 oxide) same (etch\$3 or removed) - 4732 hto or high adj2 temperature adj2 oxide - 10404321 benefit or advantag\$5 - 10404321 benefit or advantag\$5 - 140 (hto or high adj2 temperature adj2 oxide) with (benefit or advantag\$5) - 133420 gate adj5 (insulat\$4 or di\$lelectric or oxide or "sio.sub."\$1) - 133420 (hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$lelectric or oxide or "sio.sub."\$1) - 128 (hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$lelectric or oxide or "sio.sub."\$1) - 128 (hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$lelectric or oxide or "sio.sub."\$1) - 128 (hto or high adj2 temperature adj2 oxide) with teos - 128 (hto or high adj2 temperature adj2 oxide) with teos - 128 (hto or high adj2 temperature adj2 oxide) with teos - 128 (hto or high adj2 temperature adj2 oxide) with teos - 128 (hto or high adj2 temperature adj2 oxide) with teos - 128 (hto or high adj2 temperature adj2 oxide) with teos - 128 (hto or high adj2 temperature adj2 oxide) with teos - 128 (hto or high adj2 temperature adj2 oxide) with teos	-	182885	bhf or boe or (hf or hydrofluoric)	USPAT;	2004/09/24 16:25
- 101 (bhf or boe or (hf or hydrofluoric)) same (hto or high adj2 temperature adj2 oxide) same (etch\$3 or removed) - 4732 hto or high adj2 temperature adj2 oxide - 10404321 benefit or advantag\$5 - 1040 (hto or high adj2 temperature adj2 oxide) with (benefit or advantag\$5 - 133420 gate adj5 (insulat\$4 or di\$lelectric or oxide or "sio.sub."\$1) - 302 (hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$lelectric or oxide or "sio.sub."\$1) - 228 (hto or high adj2 temperature adj2 oxide) with teos DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USP				US-PGPUB;	1
101				EPO; JPO;	
Chef or boe or (hf or hydrofluoric) same (hot or high adj2 temperature adj2 oxide) Same (etch\$3 or removed) Same (etch\$3 or etch\$4:08 Same (etch\$4:08 Same				1	İ
(hto or high adj2 temperature adj2 oxide) same (etch\$3 or removed) - 4732 hto or high adj2 temperature adj2 oxide - 10404321 benefit or advantag\$5 - 10404321 benefit or advantag\$5 - 1040 (hto or high adj2 temperature adj2 oxide) with (benefit or advantag\$5) - 133420 gate adj5 (insulat\$4 or di\$lelectric or oxide or "sio.sub."\$1) - 133420 (hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$lelectric or oxide or "sio.sub."\$1) - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos					
Same (etch\$3 or removed)	-	101			2004/09/24 16:26
DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT;					
TBM TDB USPAT; USPAT; USPAT; USPROPUB; EPO; JPO; DERWENT; IBM TDB USPROPUB; EPO; JPO; DER			same (etch\$3 or removed)		
- 4732 hto or high adj2 temperature adj2 oxide					
US-PGPUB; EFO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EFO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EFO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EFO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EFO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EFO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EFO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EFO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EFO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EFO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EFO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EFO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EFO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EFO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EFO; JPO; DERWENT;		4732	hto or high adi? tomporature adi? evide		2004/09/25 14:08
EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT;		4/32	l lico of high adjz temperature adjz oxide		2004/03/25 14.08
DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;					
- 10404321 benefit or advantag\$5					
- 10404321 benefit or advantag\$5 USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JP					-
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	_	10404321	benefit or advantag\$5		2004/09/25 14:08
- 140 (hto or high adj2 temperature adj2 oxide) with (benefit or advantag\$5) - 133420 gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1) - 302 (hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1) - 302 (hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1) - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos					,,,
- 140 (hto or high adj2 temperature adj2 oxide) with (benefit or advantag\$5) - 133420 gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1) - 302 (hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1) - 302 (hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1) - 228 (hto or high adj2 temperature adj2 oxide) with teos (hto or high adj2 temperature adj2 oxide) with teos (hto or high adj2 temperature adj2 oxide) with teos DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;					
- 140 (hto or high adj2 temperature adj2 oxide) with (benefit or advantag\$5) - 133420 gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1) - 302 (hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1) - 302 (hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1) - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 229 (hto or high adj2 temperature adj2 oxide) with teos - 22004/09/25 14:18 - 2004/09/25 14:19 - 2004/09/25 14:20 USPAT; USPAT; USPAT; USPGPUB; EPO; JPO; DERWENT; USPAT; USPGPUB; EPO; JPO; DERWENT;	}				
- 140 (hto or high adj2 temperature adj2 oxide) With (benefit or advantag\$5) USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; Or oxide or "sio.sub."\$1) USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWE					
with (benefit or advantag\$5) US-PGPUB; EPO; JPO; DERWENT; IBM TDB US-PGPUB; EPO; JPO; Oxide or "sio.sub."\$1 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; Or oxide or "sio.sub."\$1 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; Or oxide or "sio.sub."\$1 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWENT;	-	140		USPĀT;	2004/09/25 14:08
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	1			US-PGPUB;	
- 133420 gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1) - 302 (hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1) - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 28 (hto or high adj2 temperature adj2 oxide) with teos - 29 (hto or high adj2 temperature adj2 oxide) with teos - 2004/09/25 14:18 - 2004/09/25 14:19 - 2004/09/25 14:20			_		
- 133420 gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1) - 302 (hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$1electric or DERWENT; with (gate adj5 (insulat\$4 or di\$1electric or DERWENT; or oxide or "sio.sub."\$1)) - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 228 (hto or high adj2 temperature adj2 oxide) with teos - 2704/09/25 14:18					
oxide or "sio.sub."\$1) Oxide or "sio.sub."\$1) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; With (gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1)) EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; With teos US-PGPUB; EPO; JPO; DERWENT;				_	
- 302 (hto or high adj2 temperature adj2 oxide) USPAT; US-PGPUB; or oxide or "sio.sub."\$1) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 228 (hto or high adj2 temperature adj2 oxide) USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	-	133420			2004/09/25 14:18
- 302 (hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1)) (hto or high adj2 temperature adj2 oxide) bERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; US-PGPUB; EPO; JPO; DERWENT; With teos US-PGPUB; EPO; JPO; DERWENT;		1	oxide or "sio.sub."\$1)		
- 302 (hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1)) (hto or high adj2 temperature adj2 oxide) (hto or high adj2 temperature adj2 oxide) with teos IBM_TDB					
- 302 (hto or high adj2 temperature adj2 oxide) USPAT; With (gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 228 (hto or high adj2 temperature adj2 oxide) USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;		1			
with (gate adj5 (insulat\$4 or di\$1electric or oxide or "sio.sub."\$1) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 228 (hto or high adj2 temperature adj2 oxide) USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	1	200	(http://html	_	2004/00/25 14 12
or oxide or "sio.sub."\$1) EPO; JPO; DERWENT; IBM_TDB - 228 (hto or high adj2 temperature adj2 oxide) USPAT; US-PGPUB; EPO; JPO; DERWENT; With teos EPO; JPO; DERWENT;	-	302			2004/09/25 14:19
DERWENT; IBM_TDB USPAT; With teos US-PGPUB; EPO; JPO; DERWENT; DERWENT; US-PGPUB; DERWENT;	1			1	
- 228 (hto or high adj2 temperature adj2 oxide) IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	1		of oxide of Sio.Sub."\$1))		
- 228 (hto or high adj2 temperature adj2 oxide) USPAT; 2004/09/25 14:20 us-PGPUB; EPO; JPO; DERWENT;	1				
with teos US-PGPUB; EPO; JPO; DERWENT;	_	228	(hto or high adi2 temperature adi2 ovide)		2004/09/25 14.20
EPO; JPO; DERWENT;		220			2001,00,20 14.20
DERWENT;					

-	25	((hto or high adj2 temperature adj2 oxide	USPAT;	2004/09/25 14:20
) with (gate adj5 (insulat\$4 or	US-PGPUB;	
		di\$lelectric or oxide or "sio.sub."\$1)))	EPO; JPO;	
		and ((hto or high adj2 temperature adj2	DERWENT;	
L	l	oxide) with teos)	IBM TDB	